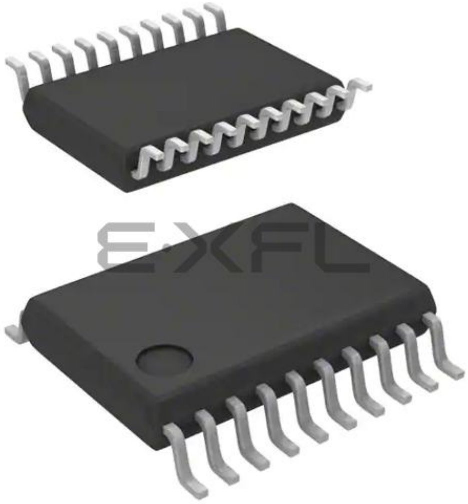
Renesas Electronics America Inc - R5F21183DSP#U0 Datasheet



What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	R8C
Core Size	16-Bit
Speed	20MHz
Connectivity	SIO, UART/USART
Peripherals	LED, POR, Voltage Detect, WDT
Number of I/O	13
Program Memory Size	12KB (12K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	768 x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	-
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	20-LSSOP (0.173", 4.40mm Width)
Supplier Device Package	20-LSSOP
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f21183dsp-u0

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R8C/18 Group, R8C/19 Group

SINGLE-CHIP 16-BIT CMOS MCU

REJ03B0124-0140
Rev.1.40
Apr 14, 2006

1. Overview

These MCUs are fabricated using a high-performance silicon gate CMOS process, embedding the R8C/Tiny Series CPU core, and is packaged in a 20-pin molded-plastic LSSOP, SDIP or a 28-pin plastic molded-HWQFN. It implements sophisticated instructions for a high level of instruction efficiency. With 1 Mbyte of address space, they are capable of executing instructions at high speed.
Furthermore, the R8C/19 Group has on-chip data flash ROM (1 KB × 2 blocks).
The difference between the R8C/18 Group and R8C/19 Group is only the presence or absence of data flash ROM. Their peripheral functions are the same.

1.1 Applications

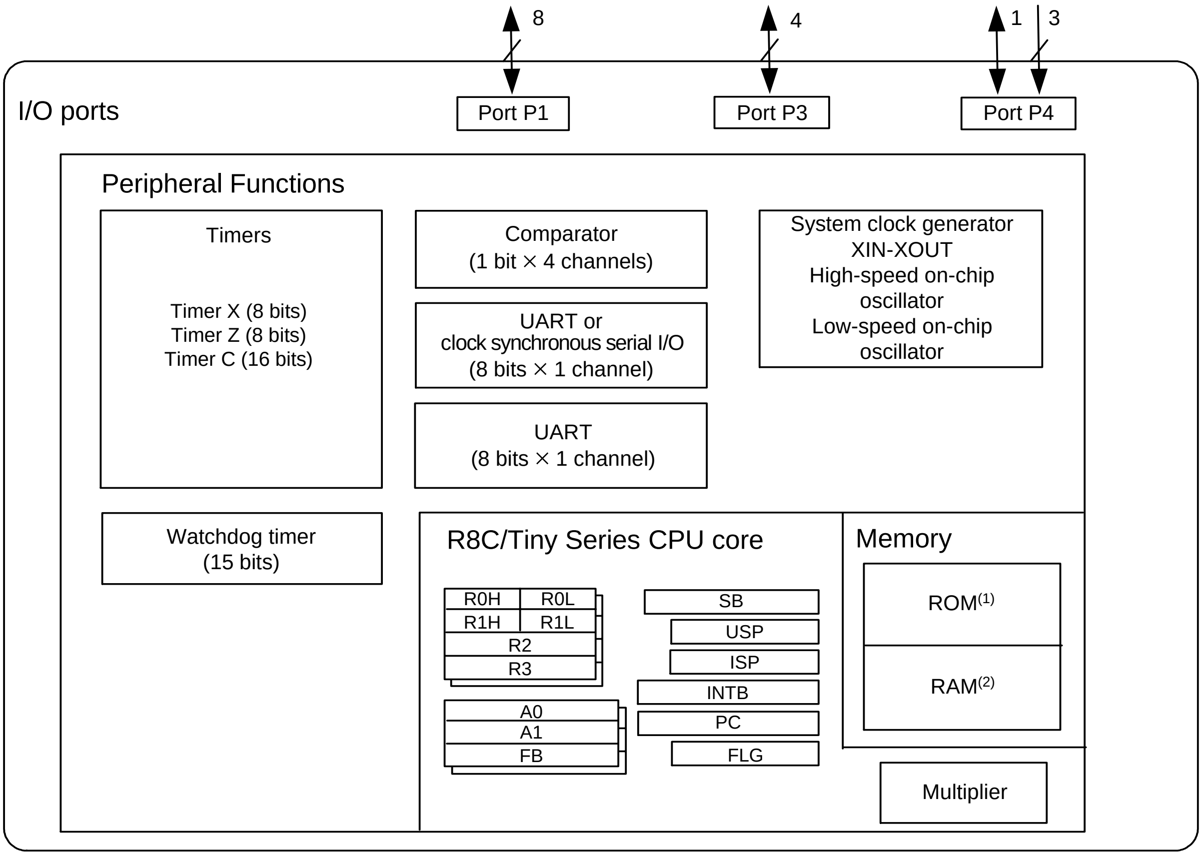
Electric household appliances, office equipment, housing equipment (sensors, security systems), general industrial equipment, audio equipment, etc.

Table 1.2 Functions and Specifications for R8C/19 Group

Item		Specification
CPU	Number of fundamental instructions	89 instructions
	Minimum instruction execution time	50 ns (f(XIN) = 20 MHz, VCC = 3.0 to 5.5 V) 100 ns (f(XIN) = 10 MHz, VCC = 2.7 to 5.5 V)
	Operation mode	Single-chip
	Address space	1 Mbyte
	Memory capacity	Refer to **Table 1.4 Product Information for R8C/19 Group**
Peripheral Functions	Ports	I/O ports: 13 pins (including LED drive port) Input port: 3 pins
	LED drive ports	I/O ports: 4 pins
	Timers	Timer X: 8 bits × 1 channel, timer Z: 8 bits × 1 channel (Each timer equipped with 8-bit prescaler) Timer C: 16 bits × 1 channel (Input capture and output compare circuits)
	Serial interfaces	1 channel Clock synchronous serial I/O, UART 1 channel UART
	Comparator	1-bit comparator: 1 circuit, 4 channels
	Watchdog timer	15 bits × 1 channel (with prescaler) Reset start selectable, count source protection mode
	Interrupts	Internal: 10 sources, External: 4 sources, Software: 4 sources, Priority levels: 7 levels
	Clock generation circuits	2 circuits • Main clock generation circuit (with on-chip feedback resistor) • On-chip oscillator (high speed, low speed) High-speed on-chip oscillator has frequency adjustment function
	Oscillation stop detection function	Main clock oscillation stop detection function
	Voltage detection circuit	On-chip
	Power-on reset circuit	On-chip
Electric Characteristics	Supply voltage	VCC = 3.0 to 5.5 V (f(XIN) = 20 MHz) VCC = 2.7 to 5.5 V (f(XIN) = 10 MHz)
	Current consumption	Typ. 9 mA (VCC = 5.0 V, f(XIN) = 20 MHz, comparator stopped) Typ. 5 mA (VCC = 3.0 V, f(XIN) = 10MHz, comparator stopped) Typ. 35 μA (VCC = 3.0 V, wait mode, peripheral clock off) Typ. 0.7 μA (VCC = 3.0 V, stop mode)
Flash Memory	Programming and erasure voltage	VCC = 2.7 to 5.5 V
	Programming and erasure endurance	10,000 times (data flash)
		1,000 times (program ROM)
Operating Ambient Temperature		-20 to 85°C -40 to 85°C (D version)
Package		20-pin molded-plastic LSSOP
		20-pin molded-plastic SDIP
		28-pin molded-plastic HWQFN

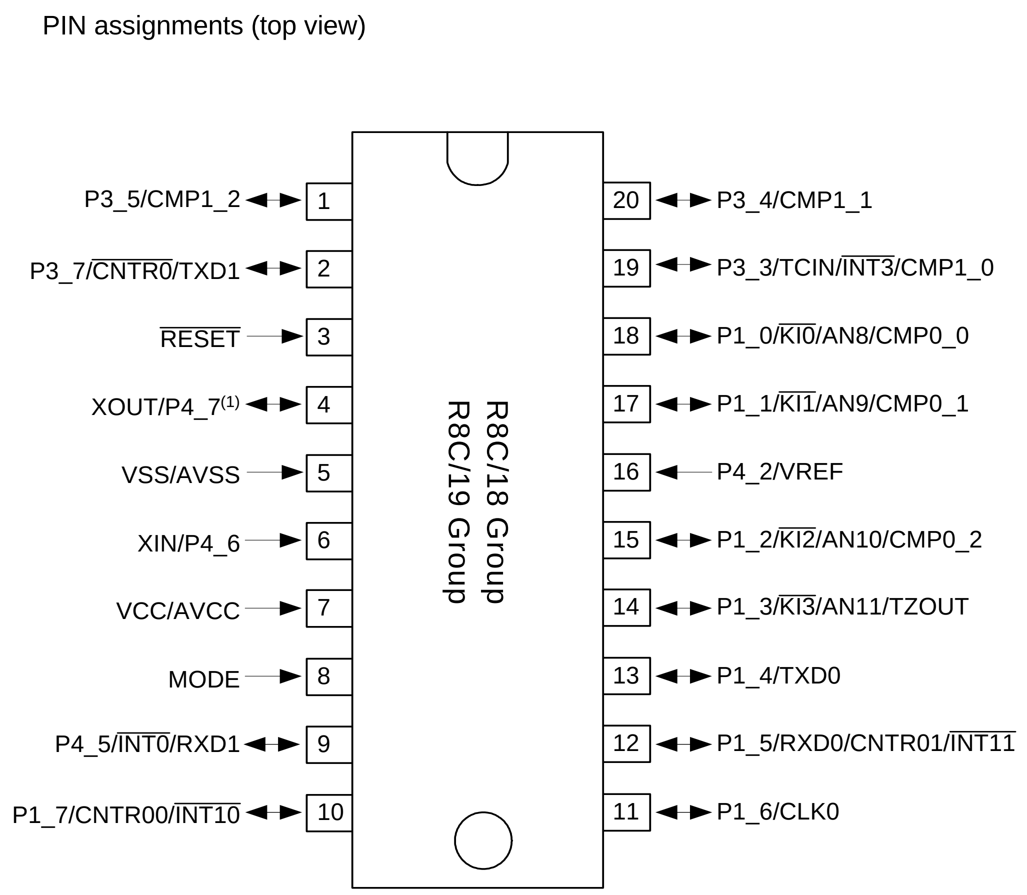
1.3 Block Diagram

Figure 1.1 shows a Block Diagram.



NOTES:
1. ROM size varies with MCU type.
2. RAM size varies with MCU type.

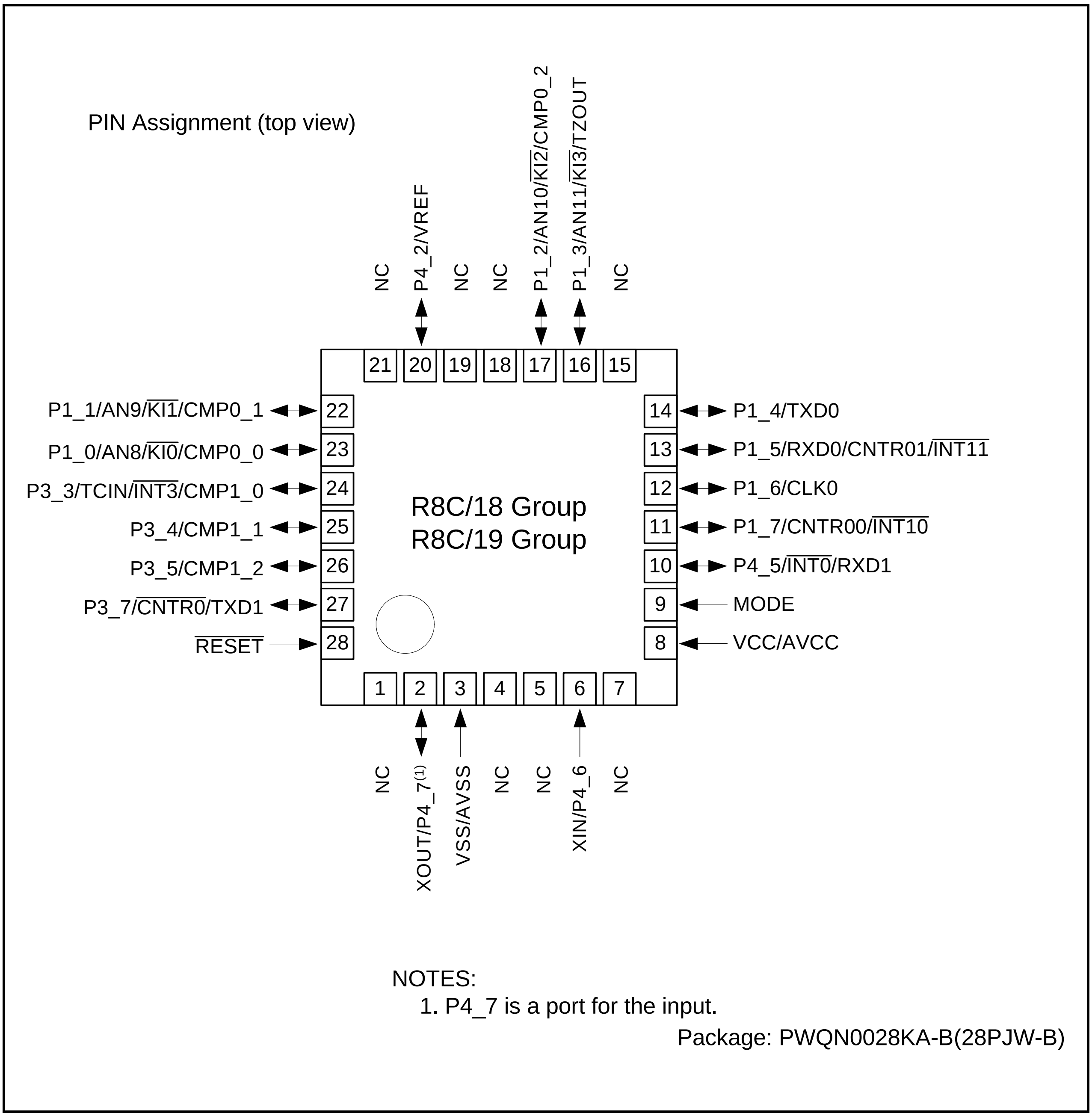
Figure 1.1 Block Diagram



NOTE:
1. P4_7 is an input-only port.

Package: PRDP0020BA-A(20P4B)

Figure 1.5 Pin Assignments for PRDP0020BA-A Package (Top View)



NOTES:
1. P4_7 is a port for the input.

Package: PWQN0028KA-B(28PJW-B)

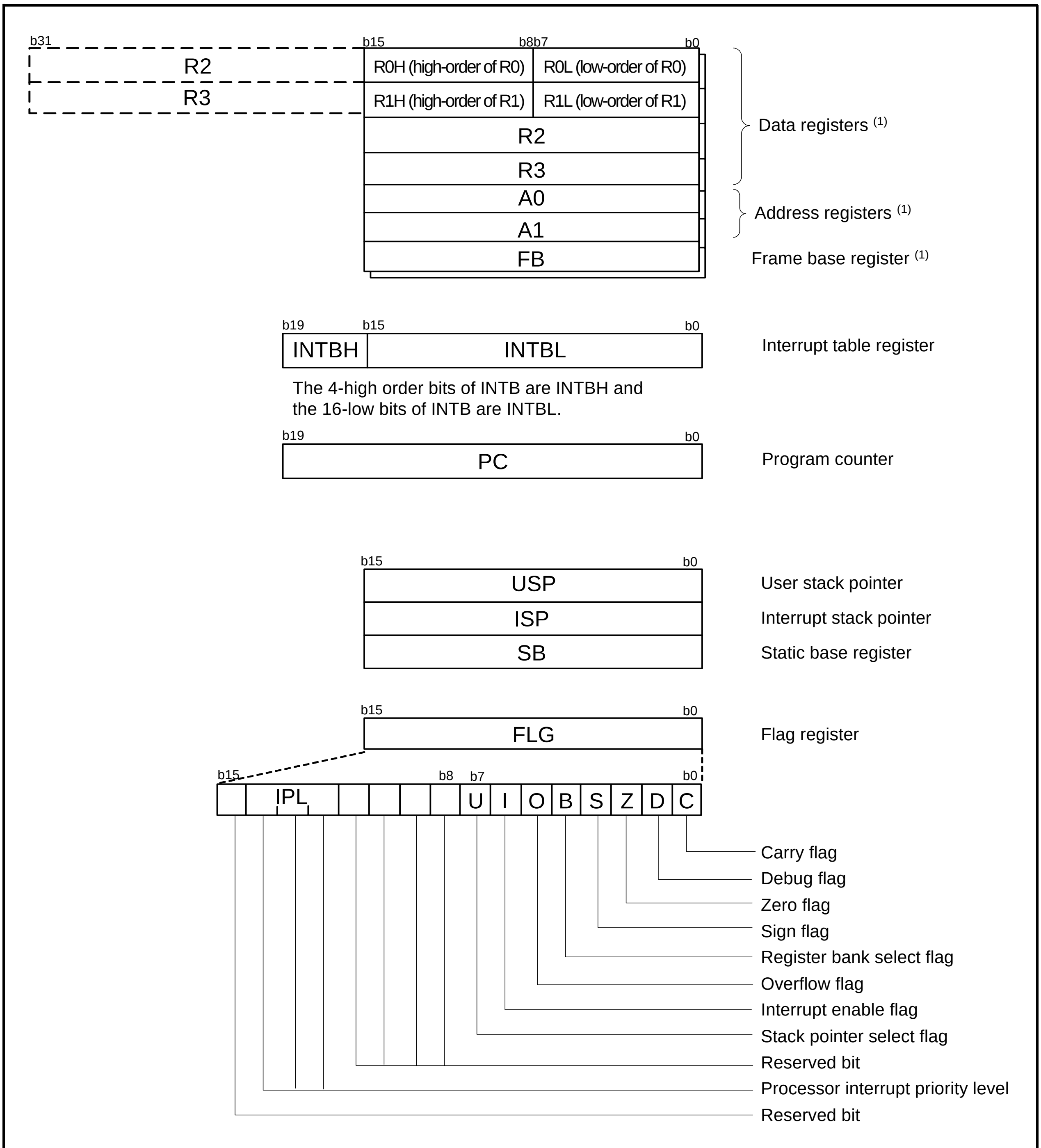
Figure 1.6 Pin Assignments for PWQN0028KA-B Package (Top View)

Table 1.7 Pin Name Information by Pin Number of PWQN0028KA-B package

Pin Number	Control Pin	Port	I/O Pin of Peripheral Function			
			Interrupt	Timer	Serial Interface	Comparator
1	NC					
2	XOUT	P4_7				
3	VSS/AVSS					
4	NC					
5	NC					
6	XIN	P4_6				
7	NC					
8	VCC/AVCC					
9	MODE					
10		P4_5	$\overline{\text{INT0}}$		RXD1	
11		P1_7	$\overline{\text{INT10}}$	CNTR00		
12		P1_6			CLK0	
13		P1_5	$\overline{\text{INT11}}$	CNTR01	RXD0	
14		P1_4			TXD0	
15	NC					
16		P1_3	$\overline{\text{KI3}}$	TZOUT		AN11
17		P1_2	$\overline{\text{KI2}}$	CMP0_2		AN10
18	NC					
19	NC					
20	VREF	P4_2				
21	NC					
22		P1_1	$\overline{\text{KI1}}$	CMP0_1		AN9
23		P1_0	$\overline{\text{KI0}}$	CMP0_0		AN8
24		P3_3	$\overline{\text{INT3}}$	TCIN/CMP1_0		
25		P3_4		CMP1_1		
26		P3_5		CMP1_2		
27		P3_7		$\overline{\text{CNTR0}}$	TXD1	
28	$\overline{\text{RESET}}$					

2. Central Processing Unit (CPU)

Figure 2.1 shows the CPU Registers. The CPU contains 13 registers. R0, R1, R2, R3, A0, A1, and FB configure a register bank. There are two sets of register bank.



NOTE:
1. These registers comprise a register bank. There are two register banks.

Figure 2.1 CPU Registers

2.8.7 Interrupt Enable Flag (I)

The I flag enables maskable interrupts.
Interrupts are disabled when the I flag is set to 0, and are enabled when the I flag is set to 1. The I flag is set to 0 when an interrupt request is acknowledged.

2.8.8 Stack Pointer Select Flag (U)

ISP is selected when the U flag is set to 0; USP is selected when the U flag is set to 1.
The U flag is set to 0 when a hardware interrupt request is acknowledged or the INT instruction of software interrupt numbers 0 to 31 is executed.

2.8.9 Processor Interrupt Priority Level (IPL)

IPL is 3 bits wide, assigns processor interrupt priority levels from level 0 to level 7.
If a requested interrupt has higher priority than IPL, the interrupt is enabled.

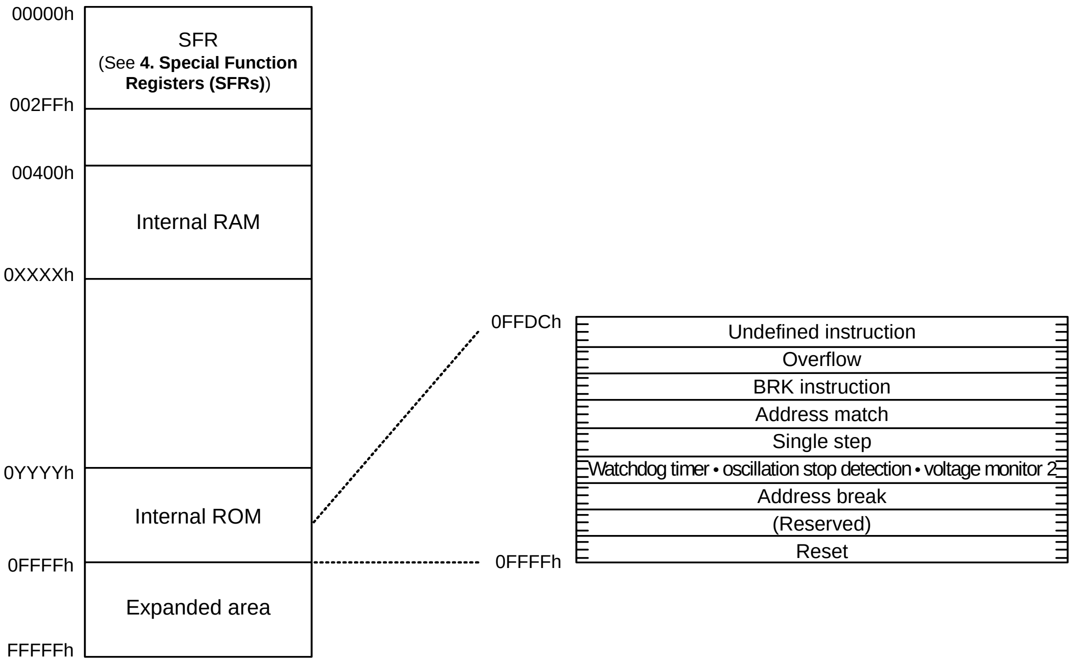
2.8.10 Reserved Bit

If necessary, set to 0. When read, the content is undefined.

3. Memory

3.1 R8C/18 Group

Figure 3.1 is a Memory Map of R8C/18 Group. The R8C/18 Group has 1 Mbyte of address space from addresses 00000h to FFFFFh.
The internal ROM area is allocated lower addresses, beginning with address 0FFFFh. For example, a 16-Kbyte internal ROM is allocated addresses 0C000h to 0FFFFh.
The fixed interrupt vector table is allocated addresses 0FFDCh to 0FFFFh. They store the starting address of each interrupt routine.
The internal RAM is allocated higher addresses, beginning with address 00400h. For example, a 1-Kbyte internal RAM area is allocated addresses 00400h to 007FFh. The internal RAM is used not only for storing data but also for calling subroutines and as stacks when interrupt requests are acknowledged.
Special function registers (SFRs) are allocated addresses 00000h to 002FFh. The peripheral function control registers are allocated here. All addresses within the SFR, which have nothing allocated are reserved for future use and cannot be accessed by users.



NOTE:
1. The blank regions are reserved. Do not access locations in these regions.

Part Number	Internal ROM		Internal RAM	
	Size	Address 0YYYYh	Size	Address 0XXXXh
R5F21184SP, R5F21184DSP, R5F21184DD, R5F21184NP	16 Kbytes	0C000h	1 Kbyte	007FFh
R5F21183SP, R5F21183DSP, R5F21183DD, R5F21183NP	12 Kbytes	0D000h	768 bytes	006FFh
R5F21182SP, R5F21182DSP, R5F21182DD, R5F21182NP	8 Kbytes	0E000h	512 bytes	005FFh
R5F21181SP, R5F21181DSP, R5F21181DD	4 Kbytes	0F000h	384 bytes	0057Fh

Figure 3.1 Memory Map of R8C/18 Group

3.2 R8C/19 Group

Figure 3.2 is a Memory Map of R8C/19 Group. The R8C/19 group has 1 Mbyte of address space from addresses 00000h to FFFFFh.

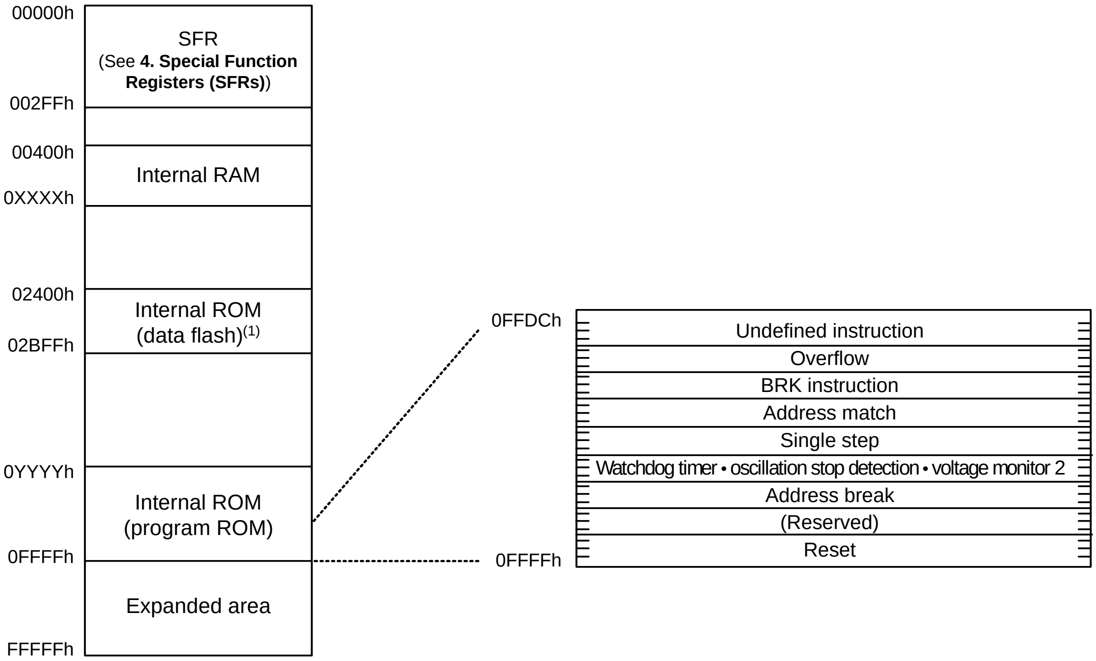
The internal ROM (program ROM) is allocated lower addresses, beginning with address 0FFFFh. For example, a 16-Kbyte internal ROM area is allocated addresses 0C000h to 0FFFFh.

The fixed interrupt vector table is allocated addresses 0FFDCh to 0FFFFh. They store the starting address of each interrupt routine.

The internal ROM (data flash) is allocated addresses 02400h to 02BFFh.

The internal RAM is allocated higher addresses, beginning with address 00400h. For example, a 1-Kbyte internal RAM area is allocated addresses 00400h to 007FFh. The internal RAM is used not only for storing data but also for calling subroutines and as stacks when interrupt requests are acknowledged.

Special function registers (SFRs) are allocated addresses 00000h to 002FFh. The peripheral function control registers are allocated here. All addresses within the SFR, which have nothing allocated are reserved for future use and cannot be accessed by users.



NOTES:
1. Data flash block A (1 Kbyte) and B (1 Kbyte) are shown.
2. The blank regions are reserved. Do not access locations in these regions.

Part Number	Internal ROM		Internal RAM	
	Size	Address 0YYYYh	Size	Address 0XXXXh
R5F21194SP, R5F21194DSP, R5F21194DD, R5F21194NP	16 Kbytes	0C000h	1 Kbyte	007FFh
R5F21193SP, R5F21193DSP, R5F21193DD, R5F21193NP	12 Kbytes	0D000h	768 bytes	006FFh
R5F21192SP, R5F21192DSP, R5F21192DD, R5F21192NP	8 Kbytes	0E000h	512 bytes	005FFh
R5F21191SP, R5F21191DSP, R5F21191DD	4 Kbytes	0F000h	384 bytes	0057Fh

Figure 3.2 Memory Map of R8C/19 Group

5. Electrical Characteristics

Table 5.1 Absolute Maximum Ratings

Symbol	Parameter	Condition	Rated Value	Unit
V_{CC}	Supply voltage	$V_{CC} = AV_{CC}$	-0.3 to 6.5	V
AV_{CC}	Analog supply voltage	$V_{CC} = AV_{CC}$	-0.3 to 6.5	V
V_I	Input voltage		-0.3 to V_{CC}+0.3	V
V_O	Output voltage		-0.3 to V_{CC}+0.3	V
P_d	Power dissipation	T_{opr} = 25°C	300	mW
T_{opr}	Operating ambient temperature		-20 to 85 / -40 to 85 (D version)	°C
T_{stg}	Storage temperature		-65 to 150	°C

Table 5.2 Recommended Operating Conditions

Symbol	Parameter		Conditions	Standard			Unit
				Min.	Typ.	Max.	
V_{CC}	Supply voltage			2.7	–	5.5	V
AV_{CC}	Analog supply voltage			–	V_{CC}	–	V
V_{SS}	Supply voltage			–	0	–	V
AV_{SS}	Analog supply voltage			–	0	–	V
V_{IH}	Input “H” voltage			0.8V_{CC}	–	V_{CC}	V
V_{IL}	Input “L” voltage			0	–	0.2V_{CC}	V
$I_{OH(sum)}$	Peak sum output “H” current	Sum of all pins I_{OH} (peak)		–	–	-60	mA
$I_{OH(peak)}$	Peak output “H” current			–	–	-10	mA
$I_{OH(avg)}$	Average output “H” current			–	–	-5	mA
$I_{OL(sum)}$	Peak sum output “L” currents	Sum of all pins I_{OL} (peak)		–	–	60	mA
$I_{OL(peak)}$	Peak output “L” currents	Except P1_0 to P1_3		–	–	10	mA
		P1_0 to P1_3	Drive capacity HIGH	–	–	30	mA
			Drive capacity LOW	–	–	10	mA
$I_{OL(avg)}$	Average output “L” current	Except P1_0 to P1_3		–	–	5	mA
		P1_0 to P1_3	Drive capacity HIGH	–	–	15	mA
			Drive capacity LOW	–	–	5	mA
$f_{(XIN)}$	Main clock input oscillation frequency		3.0 V ≤ V_{CC} ≤ 5.5 V	0	–	20	MHz
			2.7 V ≤ V_{CC} < 3.0 V	0	–	10	MHz

NOTES:

1. V_{CC} = 2.7 to 5.5 V at T_{opr} = -20 to 85 °C / -40 to 85 °C, unless otherwise specified.
2. Typical values when average output current is 100 ms.

Table 5.5 Flash Memory (Data flash Block A, Block B) Electrical Characteristics

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Program/erase endurance(2)		10,000(3)	–	–	times
–	Byte program time (Program/erase endurance ≤ 1,000 times)		–	50	400	µs
–	Byte program time (Program/erase endurance > 1,000 times)		–	65	–	µs
–	Block erase time (Program/erase endurance ≤ 1,000 times)		–	0.2	9	s
–	Block erase time (Program/erase endurance > 1,000 times)		–	0.3	–	s
$t_{d(SR-SUS)}$	Time delay from suspend request until suspend		–	–	97+CPU clock × 6 cycles	µs
–	Interval from erase start/restart until following suspend request		650	–	–	µs
–	Interval from program start/restart until following suspend request		0	–	–	ns
–	Time from suspend until program/erase restart		–	–	3+CPU clock × 4 cycles	µs
–	Program, erase voltage		2.7	–	5.5	V
–	Read voltage		2.7	–	5.5	V
–	Program, erase temperature		-20(8)	–	85	°C
–	Data hold time(9)	Ambient temperature = 55 °C	20	–	–	year

NOTES:
1. V_{CC} = 2.7 to 5.5 V at T_{opr} = -20 to 85 °C / -40 to 85 °C, unless otherwise specified.
2. Definition of programming/erasure endurance
   The programming and erasure endurance is defined on a per-block basis.
   If the programming and erasure endurance is n (n = 100 or 10,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one. However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
4. If emergency processing is required, a suspend request can be generated independent of this characteristic. In that case the normal time delay to suspend can be applied to the request. However, we recommend that a suspend request with an interval of less than 650 µs is only used once because, if the suspend state continues, erasure cannot operate and the incidence of erasure error rises.
5. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. It is also advisable to retain data on the erase count of each block and limit the number of erase operations to a certain number.
6. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
7. Customers desiring programming/erasure failure rate information should contact their Renesas technical support representative.
8. -40 °C for D version.
9. The data hold time includes time that the power supply is off or the clock is not supplied.

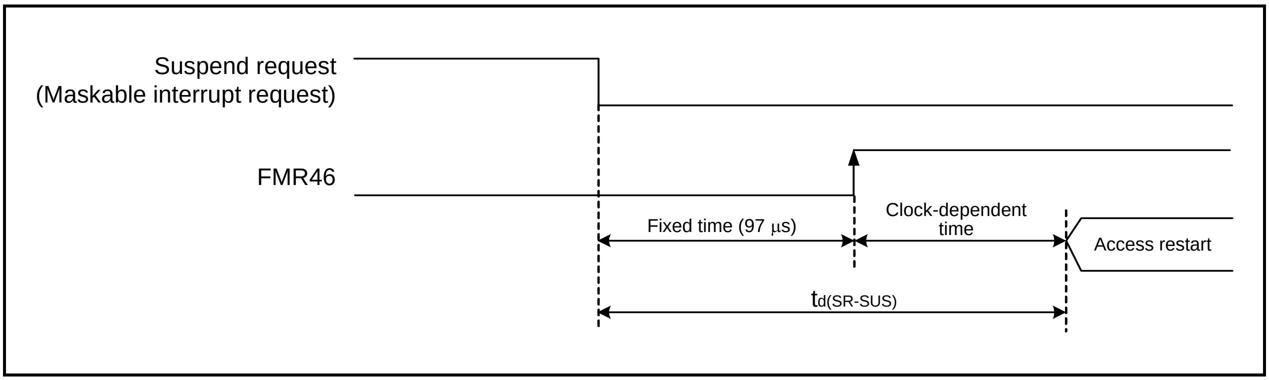


Figure 5.2 Transition Time to Suspend

Timing Requirements
(Unless Otherwise Specified: V_{CC} = 5 V, V_{SS} = 0 V at Ta = 25 °C) [V_{CC} = 5 V]

Table 5.14 XIN Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(XIN)}$	XIN input cycle time	50	–	ns
$t_{WH(XIN)}$	XIN input “H” width	25	–	ns
$t_{WL(XIN)}$	XIN input “L” width	25	–	ns

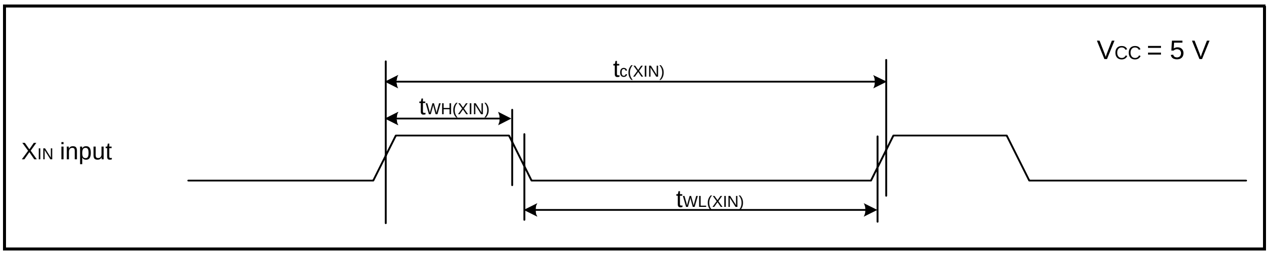


Figure 5.4 XIN Input Timing Diagram when V_{CC} = 5 V

Table 5.15 CNTR0 Input, CNTR1 Input, $\overline{\text{INT1}}$ Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(CNTR0)}$	CNTR0 input cycle time	100	–	ns
$t_{WH(CNTR0)}$	CNTR0 input “H” width	40	–	ns
$t_{WL(CNTR0)}$	CNTR0 input “L” width	40	–	ns

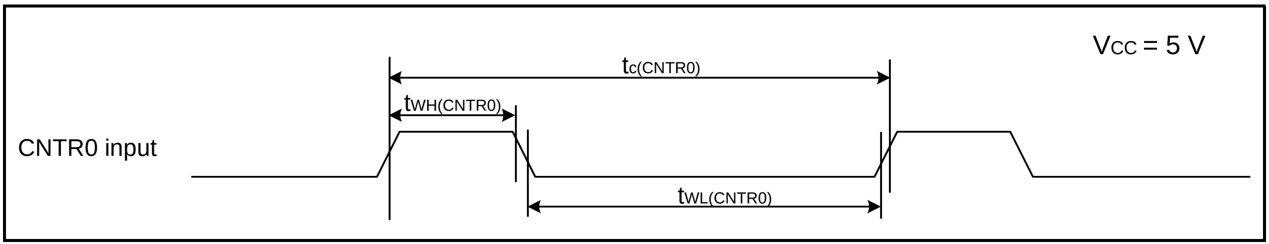


Figure 5.5 CNTR0 Input, CNTR1 Input, $\overline{\text{INT1}}$ Input Timing Diagram when V_{CC} = 5 V

Table 5.16 TCIN Input, $\overline{\text{INT3}}$ Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TCIN)}$	TCIN input cycle time	400(1)	–	ns
$t_{WH(TCIN)}$	TCIN input “H” width	200(2)	–	ns
$t_{WL(TCIN)}$	TCIN input “L” width	200(2)	–	ns

NOTES:
1. When using timer C input capture mode, adjust the cycle time to (1/timer C count source frequency x 3) or above.
2. When using timer C input capture mode, adjust the pulse width to (1/timer C count source frequency x 1.5) or above.

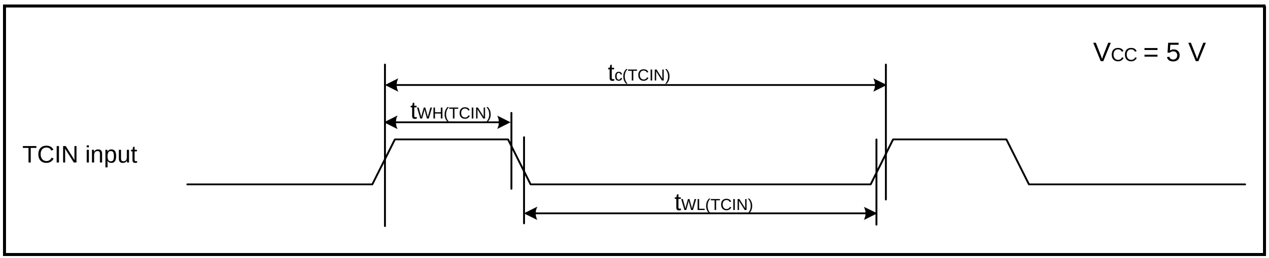


Figure 5.6 TCIN Input, $\overline{\text{INT3}}$ Input Timing Diagram when V_{CC} = 5 V

Table 5.19 Electrical Characteristics (3) [VCC = 3V]

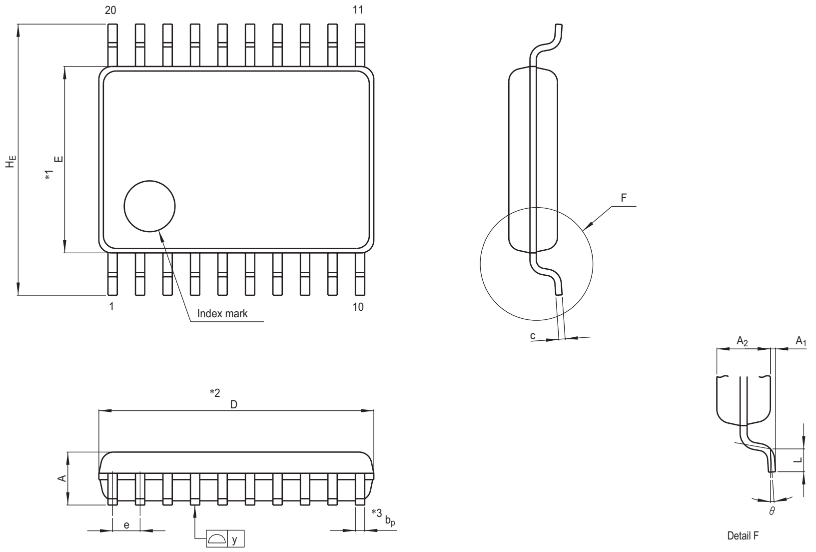
Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
VOH	Output "H" voltage	Except XOUT	IOH = -1 mA		VCC – 0.5	–	VCC	V
		XOUT	Drive capacity HIGH	IOH = -0.1 mA	VCC – 0.5	–	VCC	V
			Drive capacity LOW	IOH = -50 µA	VCC – 0.5	–	VCC	V
VOL	Output "L" voltage	Except P1_0 to P1_3, XOUT	IOL = 1mA		–	–	0.5	V
		P1_0 to P1_3	Drive capacity HIGH	IOL = 2 mA	–	–	0.5	V
			Drive capacity LOW	IOL = 1 mA	–	–	0.5	V
		XOUT	Drive capacity HIGH	IOL = 0.1 mA	–	–	0.5	V
			Drive capacity LOW	IOL = 50 µA	–	–	0.5	V
VT+-VT-	Hysteresis	$\overline{\text{INT0}}$, $\overline{\text{INT1}}$, $\overline{\text{INT2}}$, $\overline{\text{INT3}}$, $\overline{\text{KI0}}$, $\overline{\text{KI1}}$, $\overline{\text{KI2}}$, $\overline{\text{KI3}}$, CNTR0, CNTR1, TCIN, RXD0			0.2	–	0.8	V
		$\overline{\text{RESET}}$			0.2	–	1.8	V
IIH	Input "H" current		VI = 3 V		–	–	4.0	µA
IIL	Input "L" current		VI = 0 V		–	–	-4.0	µA
RPULLUP	Pull-up resistance		VI = 0 V		66	160	500	kΩ
RfXIN	Feedback resistance	XIN			–	3.0	–	MΩ
fRING-S	Low-speed on-chip oscillator frequency				40	125	250	kHz
VRAM	RAM hold voltage		During stop mode		2.0	–	–	V

NOTE:

1. VCC = 2.7 to 3.3 V at Topr = -20 to 85 °C / -40 to 85 °C, f(XIN) = 10 MHz, unless otherwise specified.

Package Dimensions

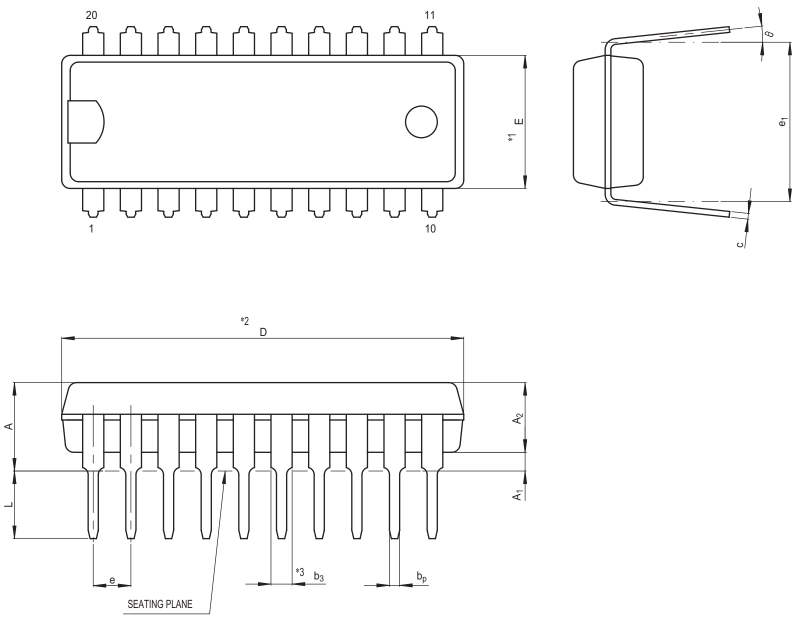
JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
P-LSSOP20-4.4x6.5-0.65	PLSP0020JB-A	20P2F-A	0.1g



NOTE)
1. DIMENSIONS "*1" AND "*2" DO NOT INCLUDE MOLD FLASH.
2. DIMENSION "*3" DOES NOT INCLUDE TRIM OFFSET.

Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	6.4	6.5	6.6
E	4.3	4.4	4.5
A_2	—	1.15	—
A	—	—	1.45
A_1	0	0.1	0.2
b_p	0.17	0.22	0.32
c	0.13	0.15	0.2
θ	0°	—	10°
H_E	6.2	6.4	6.6
e	0.53	0.65	0.77
y	—	—	0.10
L	0.3	0.5	0.7

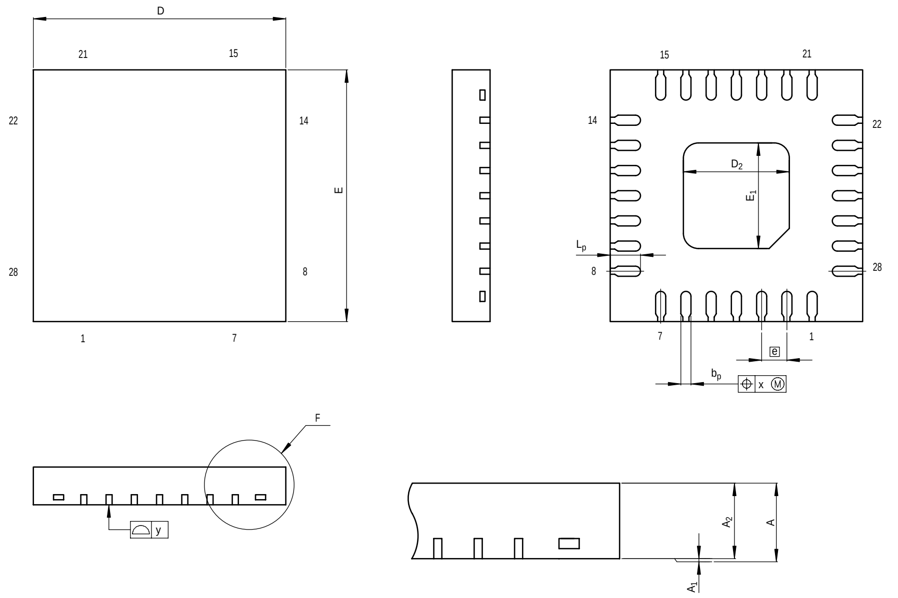
JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
P-SDIP20-6.3x19-1.78	PRDP0020BA-A	20P4B	1.0g



NOTE)
1. DIMENSIONS "*1" AND "*2" DO NOT INCLUDE MOLD FLASH.
2. DIMENSION "*3" DOES NOT INCLUDE TRIM OFFSET.

Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
e_1	7.32	7.62	7.92
D	18.8	19.0	19.2
E	6.15	6.3	6.45
A	—	—	4.5
A_1	0.51	—	—
A_2	—	3.3	—
b_p	0.38	0.48	0.58
b_3	0.9	1.0	1.3
c	0.22	0.27	0.34
θ	0°	—	15°
e	1.528	1.778	2.028
L	3.0	—	—

JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
P-HWQFN28-5x5-0.50	PWQN0028KA-B	28PJW-B	0.05g



Detail F

Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	4.9	5.0	5.1
E	4.9	5.0	5.1
A_2	—	0.75	—
A	—	—	0.8
A_1	0	0	0.05
b_p	0.15	0.2	0.25
e	—	0.5	—
L_p	0.5	0.6	0.7
x	—	—	0.05
y	—	—	0.05
D_2	—	—	2.0
E_1	—	—	2.0

REVISION HISTORY | R8C/18 Group, R8C/19 Group Datasheet

Rev.	Date	Description	
		Page	Summary
0.10	Nov 15, 2004	–	First Edition issued
0.20	Jan 11, 2005	5, 6	Tables 1.3 and 1.4: The date updated
0.21	Apr 04, 2005	2, 3	Tables 1.1 and 1.2: Partly revised
		4	Figure 1.1: Partly revised
		5, 6	Tables 1.3 and 1.4: Partly revised
		5, 6	Figure 1.2 and 1.3: Partly revised
		7, 8	Figure 1.4 and 1.5: Partly revised
		10	Table 1.6: Partly revised
		16	Table 4.1: Partly revised
		17	Table 4.2: Partly revised
		18	Table 4.3: Partly revised
		20	Package Dimensions are revised
1.00	May 27, 2005	5, 6	Tables 1.3 and 1.4: Partly revised
		9	Table 1.5: Partly revised
		25	Table 5.9: Revised
		26	Table 5.10: Partly revised
		28	Table 5.13: Partly revised
		32	Table 5.20: Partly revised
1.10	Jun 09, 2005	26	Table 5.10: Partly revised
1.20	Nov 01, 2005	3	Table 1.2 Performance Outline of the R8C/19 Group; Flash Memory: (Data area) → (Data flash) (Program area) → (Program ROM) revised
		4	Figure 1.1 Block Diagram; "Peripheral Function" added, "System Clock Generation" → "System Clock Generator" revised
		6	Table 1.4 Product Information of R8C/19 Group; ROM capacity: "Program area" → "Program ROM", "Data area" → "Data flash" revised
		9	Table 1.5 Pin Description; Power Supply Input: "VCC/AVCC" → "VCC", "VSS/AVSS" → "VSS" revised Analog Power Supply Input: added
		11	Figure 2.1 CPU Register; "Reserved Area" → "Reserved Bit" revised
		13	2.8.10 Reserved Area; "Reserved Area" → "Reserved Bit" revised
		15	3.2 R8C/19 Group, Figure 3.2 Memory Map of R8C/19 Group; "Data area" → "Data flash", "Program area" → "Program ROM" revised

Rev.	Date	Description	
		Page	Summary
1.20	Nov 01, 2005	16	Table 4.1 SFR Information(1); 0009h: "XXXXXX00b" → "00h" 000Ah: "00XXX000b" → "00h" 001Eh: "XXXXX000b" → "00h" revised
		18	Table 4.3 SFR Information(3); 0085h: "Prescaler Z" → "Prescaler Z Register" 0086h: "Timer Z Secondary" → "Timer Z Secondary Register" 0087h: "Timer Z Primary" → "Timer Z Primary Register" 008Ch: "Prescaler X" → "Prescaler X Register" 008Dh: "Timer X" → "Timer X Register" 0090h, 0091h: "Timer C" → "Timer C Register" revised
		22	Table 5.4 Flash Memory (Program ROM) Electrical Characteristics; NOTES 3 and 5 revised, NOTE8 deleted
		23	Table 5.5 Flash Memory (Data flash Block A, Block B) Electrical Characteristics; NOTES 1 and 3 revised
		25	Table 5.8 Reset Circuit Electrical Characteristics (When Using Voltage Monitor 1 Reset); NOTE 2 revised
		26	Table 5.10 High-speed On-Chip Oscillator Circuit Electrical Characteristics; "High-Speed On-Chip Oscillator ..." → "High-Speed On-Chip Oscillator Frequency ..." revised NOTE 2, 3 added
		28	Table 5.13 Electrical Characteristics (2) [Vcc = 5V]; NOTE 1 deleted
		32	Table 5.20 Electrical Characteristics (4) [Vcc = 3V]; NOTE 1 deleted
1.30	Dec 16, 2005	–	Products of PWQN0028KA-B package included
		5, 6	Table 1.3, Table 1.4 revised
		24	Table 5.4 Flash Memory (Program ROM) Electrical Characteristics; Ta → Ambient temperature
		25	Table 5.5 Flash Memory (Data flash Block A, Block B) Electrical Characteristics; Ta → Ambient temperature
		30, 34	Table 5.13, Table 5.20; The title revised, Condition of Stop Mode added
		32, 36	Table 5.17, Table 5.24; td(C-Q) and tsu(D-C) revised
		37, 38	Package Dimensions revised
1.40	Apr 14, 2006	2, 3	Table 1.1, Table 1.2; Interrupts: Internal 8 → 10 sources,
		5, 6	Table 1.3, Table 1.4; Type No. added, deleted
		16, 17	Figure 3.1, Figure 3.2; Part Number added, deleted
		24, 25	Table 5.4, Table 5.5; Conditions: VCC = 5.0 V at Topr = 25 °C deleted

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